

# NCE N-Channel Enhancement Mode Power MOSFET

## Description

The NCE4080 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## **General Features**

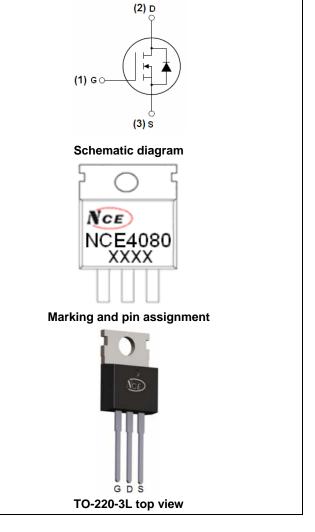
- V<sub>DS</sub> =40V,I<sub>D</sub> =80A
- R<sub>DS(ON)</sub> <6.5mΩ @ V<sub>GS</sub>=10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

### Application

- PWM
- Load Switching

#### 100% UIS TESTED!

100% ΔVds TESTED!



# Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE4080	NCE4080	TO-220-3L	-	-	-

### Absolute Maximum Ratings (T<sub>c</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	40	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι <sub>D</sub>	80	А	
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	56	А	
Pulsed Drain Current	I <sub>DM</sub>	350	А	
Maximum Power Dissipation	PD	90	W	
Derating factor		0.6	W/℃	
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	670	mJ	
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C	





#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>θJC</sub>	1.67	°C/W

#### Electrical Characteristics (T<sub>c</sub>=25<sup>°</sup>C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	40	45	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	1.2	1.8	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	5.3	6.5	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	15	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C <sub>lss</sub>	<u>)</u> ( ) () () () () () () () () () () () ()	-	4010	-	PF
Output Capacitance	Coss		-	750	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHZ	-	390	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t <sub>d(on)</sub>		-	11	-	nS
Turn-on Rise Time	tr	$V_{DD}$ =20V, R <sub>L</sub> =1 $\Omega$	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =20A 	-	38	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	11	-	nS
Total Gate Charge	Qg	N/ 001/1 00A	-	50	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	12	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	13	-	nC
Drain-Source Diode Characteristics						L
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	80	А
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	33	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	34	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negl	igible (turi	n-on is do	minated b	y LS+LD)

#### Notes:

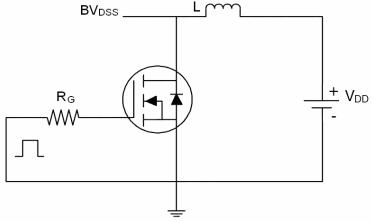
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.**  $E_{AS}$  condition : Tj=25 $^{\circ}$ C,  $V_{DD}$ =20V,  $V_{G}$ =10V, L=1mH, Rg=25 $\Omega$ ,  $I_{AS}$ =36A



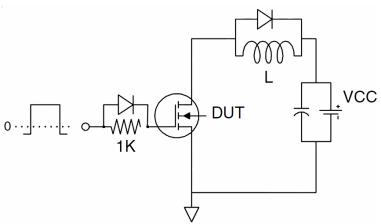
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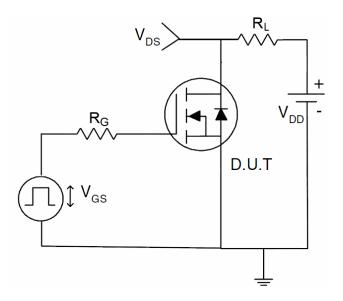
# Test circuit 1) E<sub>AS</sub> Test Circuit



# 2) Gate Charge Test Circuit



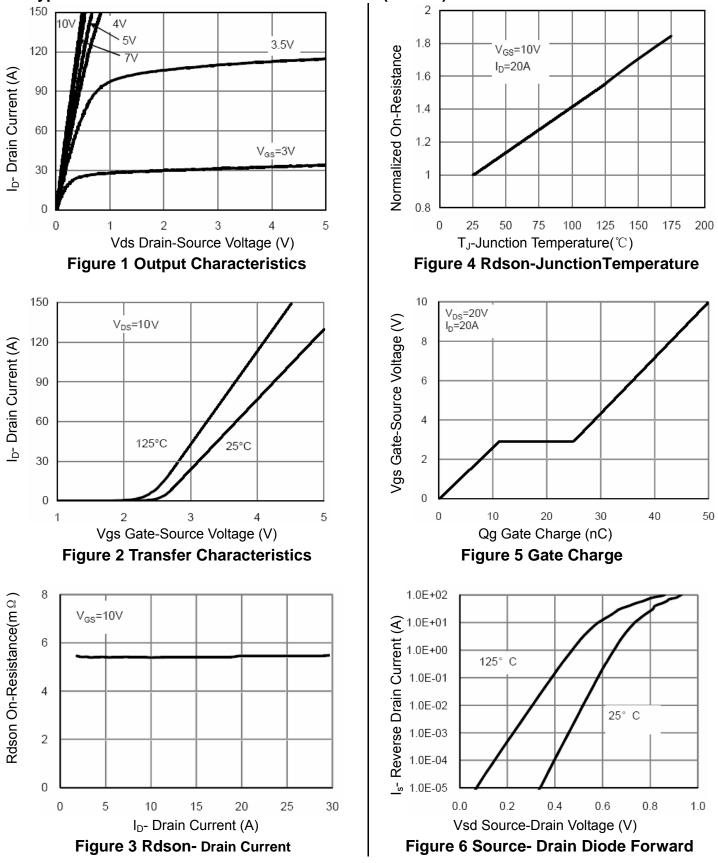
3) Switch Time Test Circuit







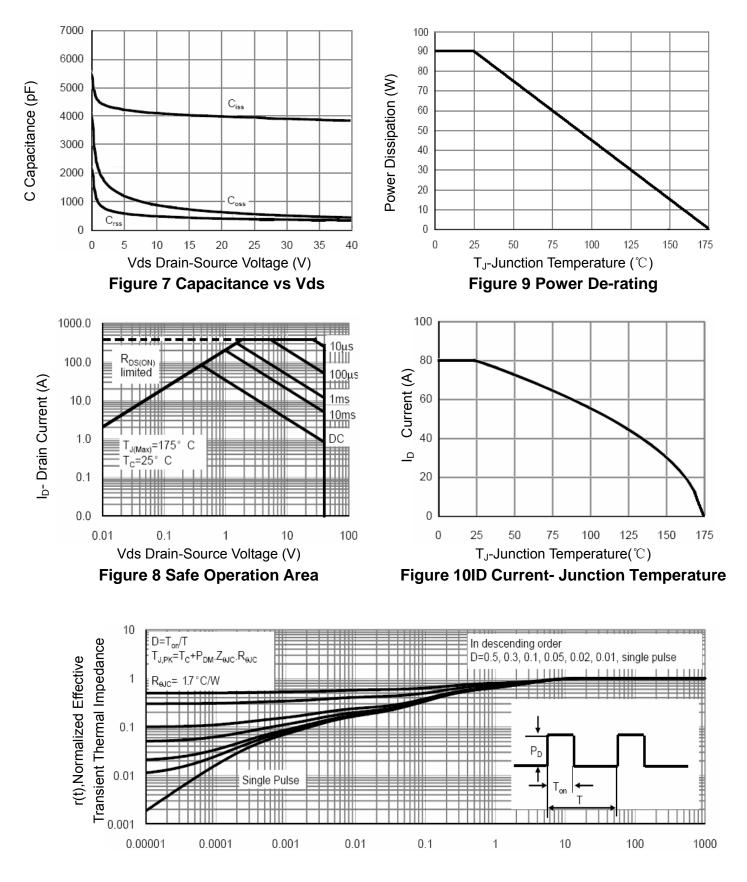
# **Typical Electrical and Thermal Characteristics (Curves)**





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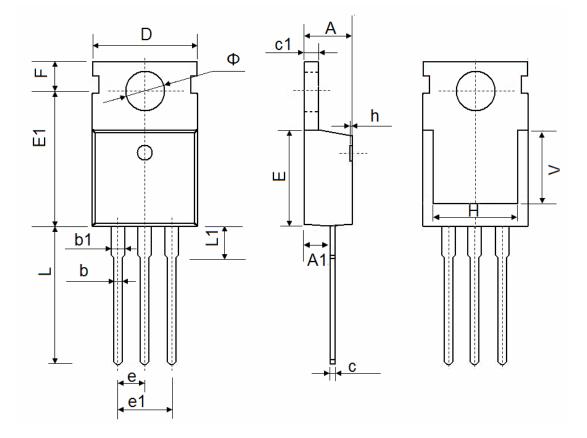
Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



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# **TO-220-3L Package Information**



Symbol	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
e	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	





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